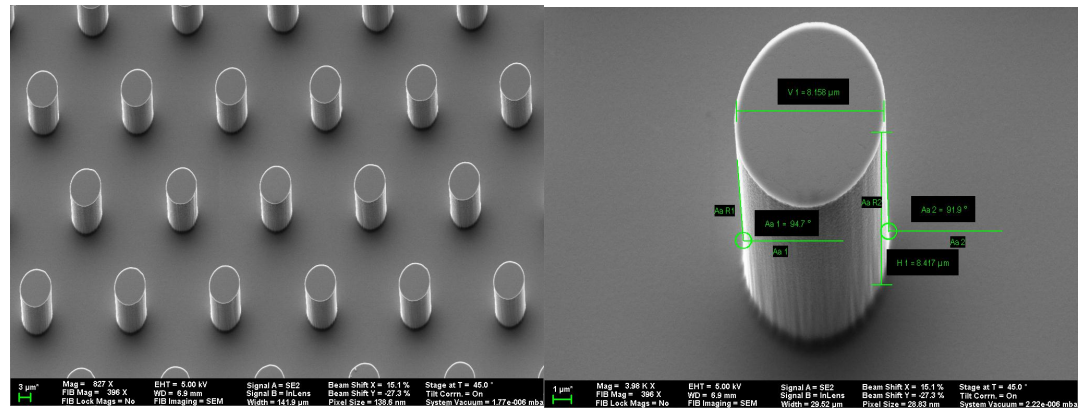


Si Micro-Pillars

Etching Mask: 1.2 μm photoresist S1813

Process Condition

Parameter	Value
C4F8 (sccm)	150
SF6 (sccm)	80
Pressure (mTorr)	20
Coil Power (W)	1200
Platen Power (W)	12
Temperature ($^{\circ}\text{C}$) (lid/wall/chuck)	40/40/21



Result

Parameter	Value
Etch Rate ($\mu\text{m}/\text{min}$)	0.7
Etch Profile	89.5 $^{\circ}$
Selectivity to Resist	10:1